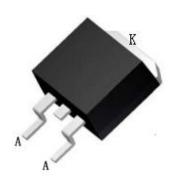
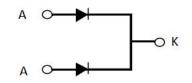


FRED Ultrafast Soft Recovery Diode, 20A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
VR	400 V	
lf(AV)	2*10A	
trr	21ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		400	V
Continuous forward current	lf(AV)	Tc =110°C	20	
Single pulse forward current	lfsm	Tc =25°C	120	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	40	
Operating junction	Tj		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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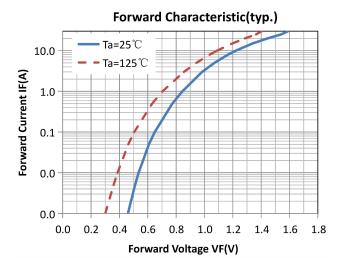


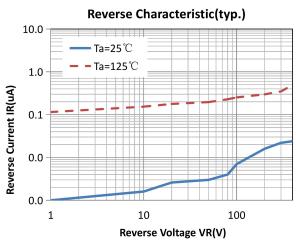
Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units	
Breakdown voltage VBR, Blocking voltage VR Forward voltage (Per Diode)	Ir=100µA	400					
	VF	Ir=10A		1.20	1.50	V	
		I _F =10 A, Tj =125°C		1.10	1.40		
Reverse leakage current(Per Diode)	lr	Vr= Vrrm			10		
		Tj=150°C, Vr=400V			100	μΑ	
Reverse recovery		I _F =0.5A, I _R =1A, I _{RR} =0.25A		30	40		
time(Per Diode)	trr	I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		21	35	ns	

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	4.2	°C/W

Electrical performance (typic)



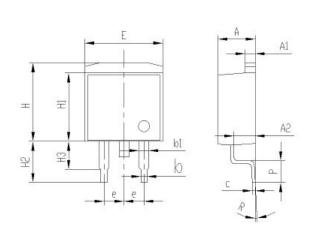


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Package Information

TO-263 PACKAGE



Symbol	Dimensions(millimeters)		
Symbol	Min.	Max.	
Α	4.50	4.90	
A1	1.17	1.37	
A2	2.40	2.80	
b	0.60	1.00	
b1	0.95	1.35	
С	0.26	0.50	
е	2.34	2.74	
Е	9.70	10.1	
Н	9.80	10.2	
H1	8.50	8.90	
H2	5.05	5.45	
H3	3.60	4.00	
R	0°	6°	
Р	2.55	2.95	

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